onsemi

ESD Protection Diode

Micro-Packaged Diodes for ESD Protection **ESD7421, SZESD7421**

The ESD7421 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, automotive sensors, infotainment, MP3 players, digital cameras and many other applications where board space comes at a premium.

Specification Features

- Low Capacitance 0.3 pF
- Low Clamping Voltage
- Low Leakage 100 nA
- Response Time is < 1 ns
- IEC61000-4-2 Level 4 ESD Protection
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

	MARKING DIAGRAM
XDFN2 (SOD-882) CASE 711AM	° _{5M} ▪
5 = Specific De M = Date Code	evice Code

Pin 1 0 Pin 2

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7421N2T5G	XDFN2 (Pb–Free)	8000 / Tape & Reel
SZESD7421N2T5G	XDFN2 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±12 ±15	kV
Total Power Dissipation on FR–5 Board (Note 1) @ $T_A = 25^{\circ}C$ Thermal Resistance, Junction–to–Ambient	P_D $R_{ hetaJA}$	300 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	ΤL	260	°C

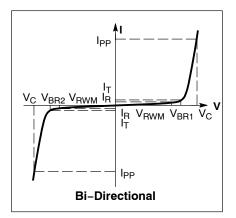
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. FR-5 = $1.0 \times 0.75 \times 0.62$ in.

See Application Note AND8308/D for further description of survivability specs.

ELECTRICAL CHARACTERISTICS

(T_A = 25° C unless otherwise noted)

	· · · · · · · · · · · · · · · · · · ·		
Symbol	Parameter		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ I _{PP}		
V _{RWM}	Working Peak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V _{BR1}	Breakdown Voltage @ I _T		
V _{BR2}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		



*See Application Note AND8308/D for detailed explanations of datasheet parameters.

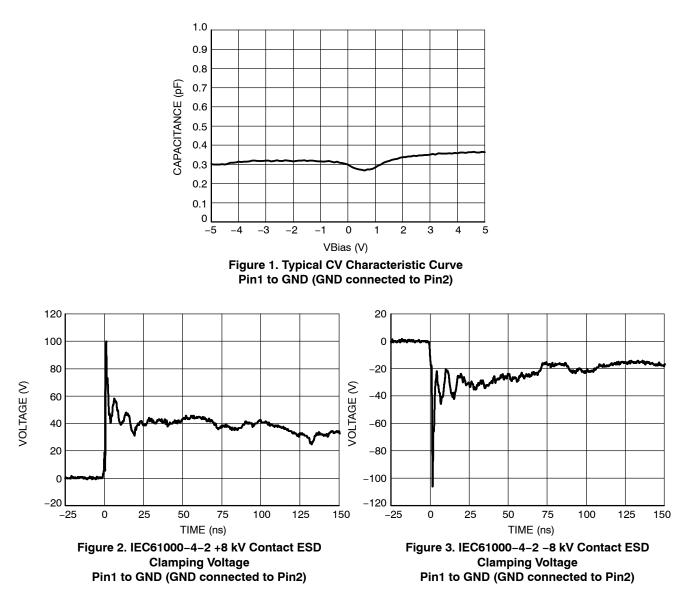
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	Pin 1 to GND Pin 2 to GND		5 5	16 10	V
Breakdown Voltage	V _{BR1}	I _T = 1 mA, Pin 1 to GND	16.5			V
Breakdown Voltage	V _{BR2}	I _T = 1 mA, Pin 2 to GND	10.5		14	V
Reverse Leakage Current	I _R	V _{RWM} = 5 V, I/O Pin to GND V _{RWM} = 16 V, Pin 1 to GND			500 1.0	nA μA
Clamping Voltage (Note 2)	V _C	IEC61000-4-2, ±8 kV Contact	See Figures 2 and 3		nd 3	
Clamping Voltage TLP (Note 3)	I _{PP} = 16 A I _{PP} = -8 A		35 38.1 -21 -29.5		V	
Junction Capacitance	CJ	VR = 0 V, f = 1 MHz between I/O Pins and GND		0.3	0.6	pF

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

For test procedure see Figure 5 and application note AND8307/D.
 ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: Z₀ = 50 Ω, t_p = 100 ns, t_r = 4 ns, averaging window; t₁ = 30 ns to t₂ = 60 ns.

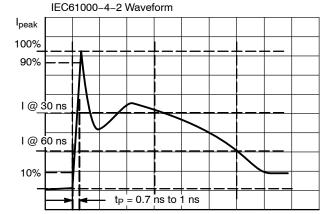
ESD7421, SZESD7421

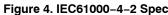


ESD7421, SZESD7421

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8





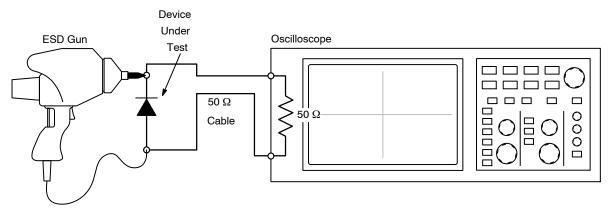


Figure 5. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. **onsemi** has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how **onsemi** creates these screenshots and how to interpret them please refer to AND8307/D.

ESD7421, SZESD7421

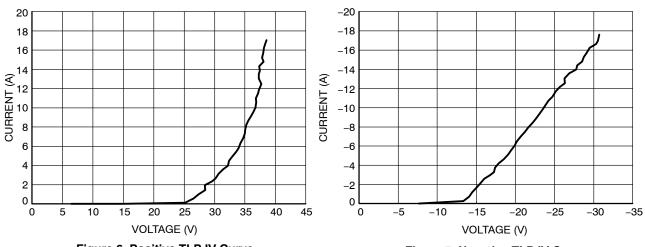


Figure 6. Positive TLP IV Curve

Figure 7. Negative TLP IV Curve

NOTE: TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100$ ns, $t_r = 300$ ps, averaging window: $t_1 = 30$ ns to $t_2 = 60$ ns.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 8. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 9 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

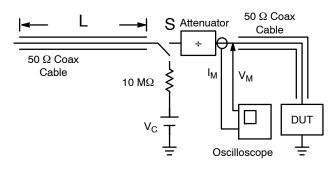


Figure 8. Simplified Schematic of a Typical TLP System

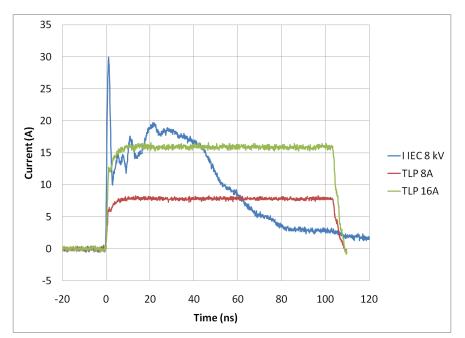


Figure 9. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

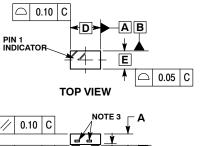


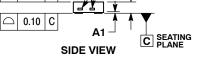
XDFN2 1.0x0.6, 0.65P (SOD-882) CASE 711AM

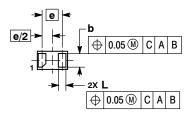
ISSUE O

DATE 29 AUG 2012

SCALE 8:1

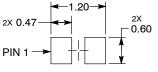




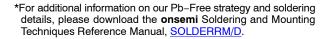


BOTTOM VIEW

RECOMMENDED **SOLDER FOOTPRINT***



DIMENSIONS: MILLIMETERS



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 EXPOSED COPPER ALLOWED AS SHOWN.



GENERIC **MARKING DIAGRAM***



- XX = Specific Device Code
- Μ = Date Code
- = Pb-Free Package
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

DOCUMENT NUMBER:	98AON82886E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION: XDFN2 1.0X0.6, 0.65P (SOD-882)			PAGE 1 OF 1	
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation				

special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>